Claims:

comprising:

a)

chamber interfaces; and

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1	1.	An apparatus for processing substrates, comprising:		
2		a)	a transfer chamber;	
3		b)	one or more load lock chambers connected to the transfer chamber;	
4		c)	one or more process chambers connected to the transfer chamber;	
5		d)	a modular plumbing tray disposed adjacent the transfer chamber and	
6	havi	having facility connections for one or more of the process chambers and the load lock		
7	chambers; and			
8		e)	a chamber tray disposed adjacent the one or more of the process	
9	chambers, load lock chambers and transfer chamber, the chamber tray having facility			
10	conn	ections	connected to one or more facility connections in the plumbing tray.	
,	2	۸		
1	2.		ethod of processing a substrate, comprising:	
2		a)	introducing a substrate into a load lock chamber from atmospheric	
3	press			
4		b)	degassing and/or pre-heating the substrate in the load lock chamber;	
5		c)	introducing the substrate into a transfer chamber; and	
6		d)	processing the substrate in one or more process chambers.	
1	3.	The	method of claim 2 further comprising:	
2		e)	introducing the substrate into the load lock chamber;	
3		f)	cooling the substrate in the load lock chamber; and then	
4		g)	venting the load lock chamber to atmospheric pressure.	
		•		
1	4.	An :	apparatus for distributing facility to devices on a processing system,	

an enclosure having at least one facility interface and one or more

- b) one or more of a process gas manifold, vacuum manifold, water manifold and a helium manifold disposed in the enclosure connected between the at least one facility interface and the one or more chamber interfaces.
- 1 5. An apparatus for distributing facility, comprising:
- a) a support frame having one or more of an electronics box, a gas panel, a
 vacuum line and a controller device disposed thereon.
- 1 6. A method of processing substrates, comprising:
- 2 a) positioning a pair of substrates on two blades on separate robots in a
- 3 processing system;
- 4 b) moving the substrates in parallel to a pair of first process chambers; and
- 5 then
- 6 c) moving the substrates in parallel to a pair of second process chambers.